

# 2SJ451

# Silicon P Channel MOS FET

REJ03G0864-0400 Rev.4.00 Sep 07, 2007

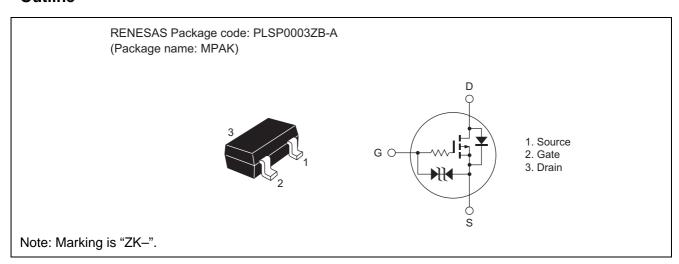
## **Description**

Low frequency power switching

### **Features**

- Low on-resistance.
- Low drive power
- 2.5 V gate drive device.
- Small package (MPAK).

### **Outline**



## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

			`
Item	Symbol	Value	Unit
Drain to source voltage	V <sub>DSS</sub>	-20	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	-0.2	A
Drain peak current	I <sub>D</sub> (pulse) Note 1	-0.4	Α
Channel dissipation	Pch	150	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

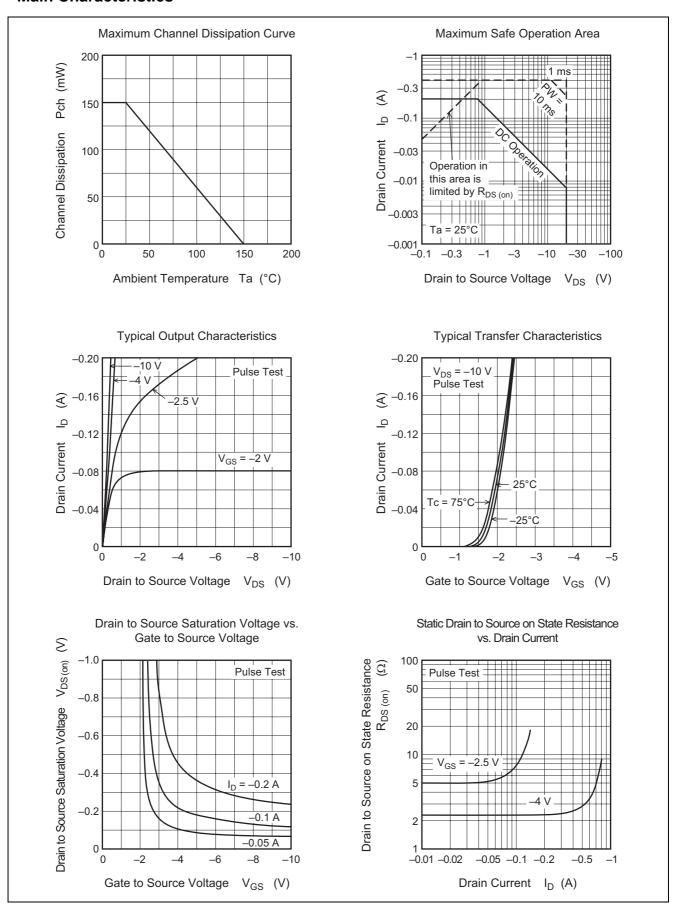
# **Electrical Characteristics**

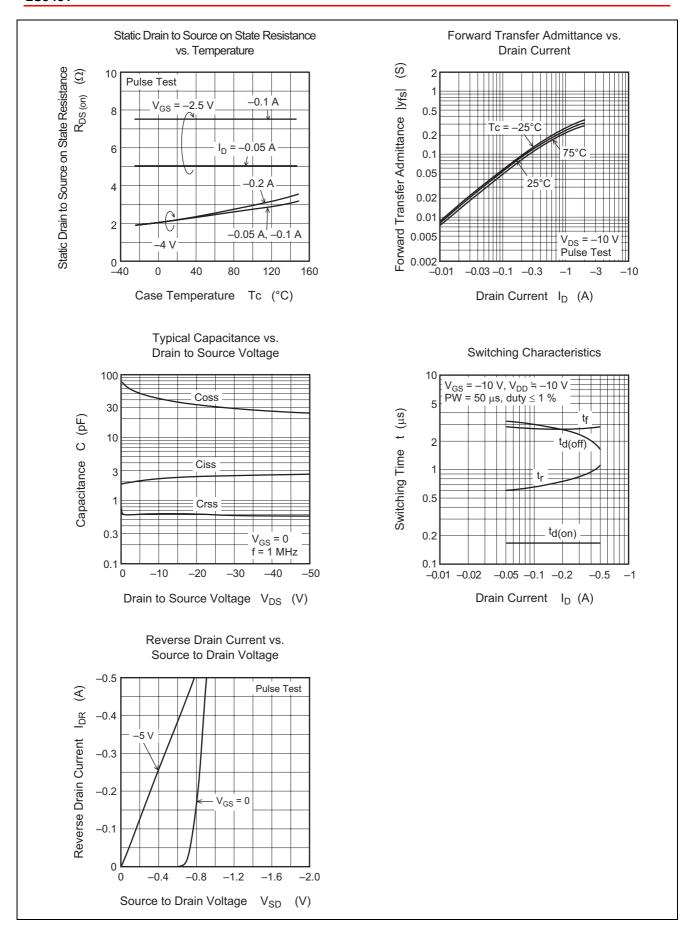
 $(Ta = 25^{\circ}C)$ 

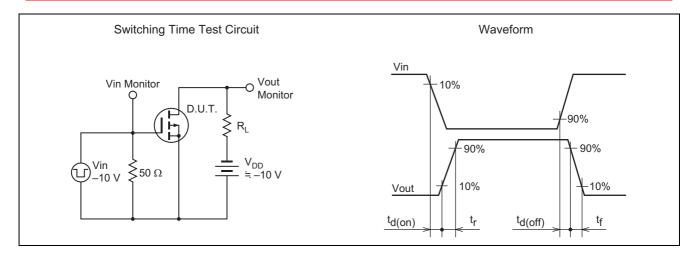
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR) DSS</sub>	-20	_	_	V	$I_D = -100 \ \mu A, \ V_{GS} = 0$
Gate to source breakdown voltage	V <sub>(BR) GSS</sub>	±20	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	-1.0	μΑ	$V_{DS} = -16 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±2.0	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	V <sub>GS (off)</sub>	-0.5	_	-1.5	V	$I_D = -10 \mu A, V_{DS} = -5 V$
Static drain to source on state resistance	R <sub>DS (on) 1</sub>	_	2.3	3.5	Ω	$I_D = -100 \text{ mA}, V_{GS} = -4 \text{ V}^{\text{Note 2}}$
	R <sub>DS (on) 2</sub>	_	5.0	9.0	Ω	$I_D = -40 \text{ mA}, V_{GS} = -2.5 \text{ V}^{\text{Note 2}}$
Forward transfer admittance	y <sub>fs</sub>	0.13	0.23	_	S	$I_D = -100 \text{ mA}, V_{DS} = -10 \text{ V}^{\text{Note 2}}$
Input capacitance	Ciss	_	2.4	_	pF	$V_{DS} = -10 \text{ V}$
Output capacitance	Coss	_	31	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	0.6	_	pF	f = 1 MHz
Turn-on delay time	t <sub>d (on)</sub>	_	170	_	ns	$I_D = -0.1 \text{ A}$
Rise time	t <sub>r</sub>	_	680	_	ns	$V_{GS} = -10 \text{ V}$
Turn-off delay time	t <sub>d (off)</sub>	_	3.0	_	μs	$R_L = 100 \Omega$
Fall time	t <sub>f</sub>	_	2.8	_	μs	

Note: 2. Pulse test

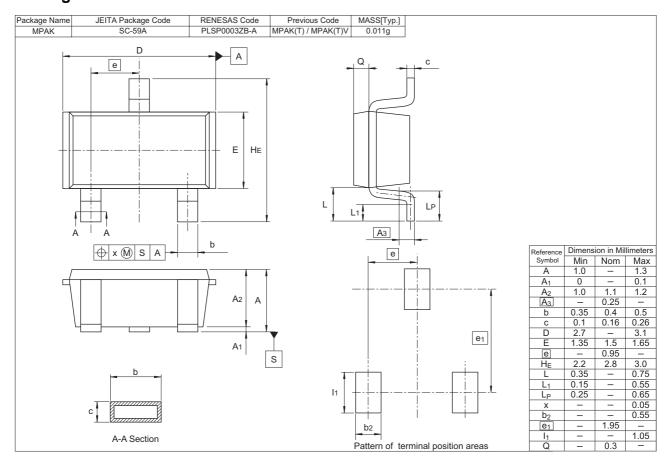
## **Main Characteristics**







## **Package Dimensions**



# **Ordering Information**

Part Name	Quantity	Shipping Container
2SJ451ZK-TL-E	3000 pcs	Taping
2SJ451ZK-TR-E	3000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

  1. This document is provided for reference purposes only so that Renesas customers may select the appropriate Renesas products for their use. Renesas neither makes warrantes or representations with respect to the accuracy or completeness of the information in this document nor grants any license to any intellectual property girbs to any other rights of representations with respect to the information in this document in this document of the purpose of the respect to the information in this document in the product data, diagrams, charts, programs, algorithms, and application circuit examples.

  3. You should not use the products of the technology described in this document for the purpose of military use. When exporting the products or technology described herein, you should follow the applicable export control laws and regulations, and procedures required by such laws and regulations, and procedures required to change without any plan protein. Before purchasing or using any Renesas products listed in this document, in the development is satisfied. The procedure is such as the development of the dev



### **RENESAS SALES OFFICES**

http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

#### Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2730-6071

**Renesas Technology Taiwan Co., Ltd.** 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510